

ABSTRACT OF DISCLOSURE

A film thickness of a gate oxide film of a lateral high breakdown voltage MOSFET of a first conduction type is formed with a thickness in which an electric field value to an absolute maximum rated voltage between a source and a drain becomes equal to or less than 4MV/cm, and a drain diffused layer is formed so that a total amount of impurities therein becomes equal to or more than $2 \times 10^{12}/\text{cm}^2$ to reduce an on-resistance of the lateral high breakdown voltage MOSFET while ensuring a breakdown voltage thereof, and to reduce an area of the lateral high breakdown voltage MOSFET.